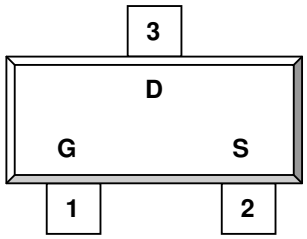
ST2303SRG

DESCRIPTION

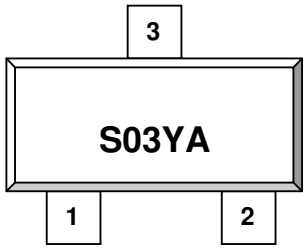
ST2303SRG is the P-Channel logic enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management, other battery powered circuits, and low in-line power loss are required. The product is in a very small outline surface mount package.

PIN CONFIGURATION
SOT-23



1.Gate 2.Source 3.Drain

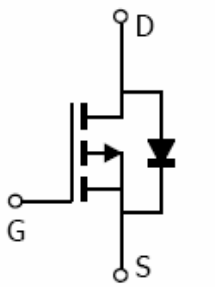
PART MARKING
SOT-23



Y: Year Code A: Process Code

FEATURE

- -30V/-2.6A, $R_{DS(ON)}$ = 95m-ohm (Typ.) @VGS = -10V
- -30V/-2.0A, $R_{DS(ON)}$ = 125m-ohm @VGS = -4.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design



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ABSOULTE MAXIMUM RATINGS (Ta = 25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain CurrentTJ=150℃)	T_A=25℃ T_A=70℃	I_D	-2.6 -2.0	A
Pulsed Drain Current		I_{DM}	-10	A
Continuous Source Current (Diode Conduction)		I_S	-1.25	A
Power Dissipation	T_A=25℃ T_A=70℃	P_D	1.25 0.8	W
Operation Junction Temperature		T_J	150	℃
Storgae Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	100	℃/W

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ELECTRICAL CHARACTERISTICS (Ta = 25℃ Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-10uA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS,I_D=-250uA	-1.0		-3.0	V
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V,V_{GS}=0V			-1	uA
		V_{DS}=-30V,V_{GS}=0V T_J=55℃			-10	
Drain-source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V,I_D=-2.6A V_{GS}=-4.5V,I_D=-2.0A		0.095 0.125		Ω
Forward Transconductance	g_{fs}	V_{DS}=-10V,I_D=-1.7V		2.4		S
Diode Forward Voltage	V_{SD}	I_S=-1.25A,V_{GS}=0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-15V V_{GS}=-10V I_D≡-1.7A		5.8	10	nC
Gate-Source Charge	Q_{gs}			0.8		
Gate-Drain Charge	Q_{gd}			1.5		
Input Capacitance	C_{iss}	V_{DS}=-15V V_{GS}=0V F=1MHz		226		pF
Output Capacitance	C_{oss}			87		
Reverse Transfer Capacitance	C_{rss}			19		
Turn-On Time	$t_{d(on)}$	V_{DD}=-15V R_L=15Ω I_D=-1.0A V_{GEN}=-10V R_G=6Ω		9	20	nS
	t_r			9	20	
Turn-Off Time	$t_{d(off)}$			18	35	
	t_f			6	20	